NSN 5962-01-123-6645

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Body Le	- 44-
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Between 0.590 inches and 0.625 inches

Body Width:

Between 0.360 inches and 0.400 inches

Body Height:

Between 0.050 inches and 0.085 inches

Maximum Power Dissipation Rating:

910.0 milliwatts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

End Application:

Radar set fscm 76301

Features Provided:

Hermetically sealed and monolithic and positive outputs and bipolar and expandable and high speed and w/enable and 3-state output

Inclosure Material:

Glass and metal

Inclosure Configuration:

Flat pack

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

17 input

Current Rating Per Characteristic:

140.00 milliamperes supply

Terminal Surface Treatment:

Solder

Voltage Rating And Type Per Characteristic:

7.0 volts power source

Capitance Rating Per Characteristic:

4.00 input picofarads and 7.00 output picofarads

Time Rating Per Chacteristic:

65.00 nanoseconds propagation delay time, low to high level output and 65.00 nanoseconds propagation delay time, high to low level output

Memory Device Type:

Pal

Test Data Document:

82577-932906 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

28 flat leads

Shelf Life:

N/a

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Demilitarization:

Yes - demil/mli

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